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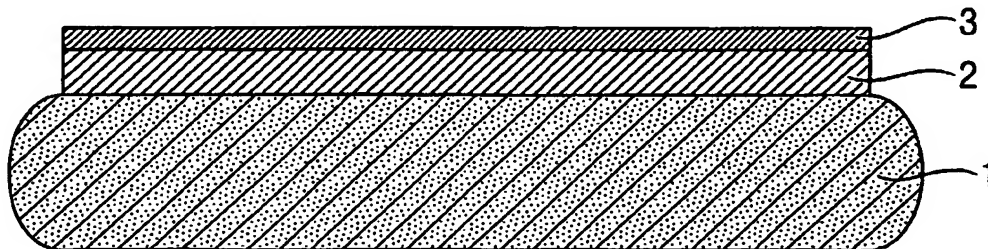
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(54) Title: TWO LAYER LTO TEMPERATURE OXIDE BACKSIDE SEAL FOR A WAFER



(57) Abstract: A two layer LTO backside seal for a wafer. The two layer LTO backside seal includes a low stress LTO layer having a first major side and a second major side, the first major side of the low stress LTO layer adjacent to one major side of the wafer. The two layer LTO backside seal further includes a high stress LTO layer having a first major side and second major side, the first major side of the high stress LTO layer adjacent the second major side of the low stress LTO layer.

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